

March 2015

FDD6690A

30V N-Channel PowerTrench^o MOSFET

General Description

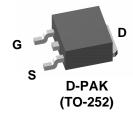
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on state resistance and yet maintain low gate charge for superior switching performance.

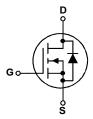
Applications

- DC/DC converter
- Motor Drives

Features

- 46 A, 30 V $R_{DS(ON)} = 12 \ m\Omega \ @ \ V_{GS} = 10 \ V$ $R_{DS(ON)} = 14 \ m\Omega \ @ \ V_{GS} = 4.5 \ V$
- · Low gate charge
- Fast Switching Speed
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter			Ratings	Units	
V _{DSS}	Drain-Source Voltage			30	V	
V _{GSS}	Gate-Source Voltage			±20	V	
I _D	Continuous Drain Current	@T _C =25°C	(Note 3)	46	А	
		@T _A =25°C	(Note 1a)	12		
		Pulsed	(Note 1a)	100		
P _D	Power Dissipation	@T _C =25°C	(Note 3)	56	W	
		@T _A =25°C	(Note 1a)	3.3		
		@T _A =25°C	(Note 1b)	1.5		
T _J , T _{STG}	Operating and Storage Junction Temperature Range			-55 to +175	°C	

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	2.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	45	
R _{e,JA}		(Note 1b)	96	

Package Marking and Ordering Information

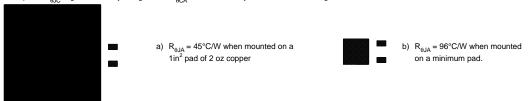
Device Marking	Device	Package	Reel Size	Tape width	Quantity
FDD6690A	FDD6690A	D-PAK (TO-252)	13"	16mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-So	urce Avalanche Ratings (Note	2)				
E _{AS}	Drain-Source Avalanche Energy	Single Pulse, V _{DD} = 15 V, I _D = 12A			180	mJ
I _{AS}	Drain-Source Avalanche Current				12	Α
Off Char	acteristics					•
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$	30			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA,Referenced to 25°C		24		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μΑ
I _{GSS}	Gate-Body Leakage	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA
On Chara	acteristics (Note 2)		•			
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	1.9	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I _D = 250 μA,Referenced to 25°C		-5		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 12 \text{ A,T}_J = 125^{\circ}\text{C}$		7.7 9.9 11.4	12 14 19	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	50			Α
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 12 \text{ A}$		47		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance			1230		pF
C _{oss}	Output Capacitance	$V_{DS} = 15 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		325		pF
C _{rss}	Reverse Transfer Capacitance	f = 1.0 MHz		150		pF
R _G	Gate Resistance	V _{GS} = 15 mV, f = 1.0 MHz		1.5		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time			10	19	ns
t _r	Turn-On Rise Time	$V_{DD} = 15 \text{ V}, \qquad I_D = 1 \text{ A},$		7	13	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		29	46	ns
t _f	Turn-Off Fall Time]		12	21	ns
Qg	Total Gate Charge			13	18	nC
Q _{gs}	Gate-Source Charge	$V_{DS} = 15V$, $I_{D} = 12 A$, $V_{GS} = 5 V$		3.5		nC
Q _{qd}	Gate-Drain Charge] VGS - 0 V		5.1		nC

Electrical Characteristics $T_A = 25$ °C unless otherwise noted Units **Symbol Parameter Test Conditions** Min Тур Max **Drain-Source Diode Characteristics and Maximum Ratings** Maximum Continuous Drain-Source Diode Forward Current 2.3 Α Drain-Source Diode Forward Voltage ٧ $V_{\text{SD}} \\$ $V_{GS} = 0 V$, $I_S = 2.3 A$ 0.76 1.2 $I_F = 12 A$, $d_{iF}/d_t = 100 \text{ A/}\mu\text{s}$ $t_{\text{rr}} \\$ Diode Reverse Recovery Time 24 nS Q_{rr} Diode Reverse Recovery Charge 13 nC

Notes:

R_{8JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of
the drain pins. R_{8JC} is guaranteed by design while R_{8CA} is determined by the user's board design.



Scale 1:1 on letter size paper

- 2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%
- 3. Maximum current is calculated as: $\sqrt{\frac{P_D}{R_{DS(ON)}}}$

where P_D is maximum power dissipation at $T_C = 25^{\circ}C$ and $R_{DS(on)}$ is at $T_{J(max)}$ and $V_{GS} = 10V$. Package current limitation is 21A

Typical Characteristics

1.6

1.4

0.6

-50

R_{DS(ON)}, NORMALIZED DRAIN-SOURCE ON-RESISTANCE I_D = 12A

V_{GS} = 10V

-25

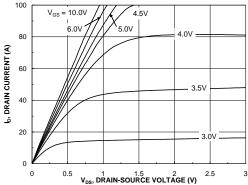


Figure 1. On-Region Characteristics



Figure 3. On-Resistance Variation withTemperature

50

 T_J , JUNCTION TEMPERATURE (°C)

75

100

125

150

25

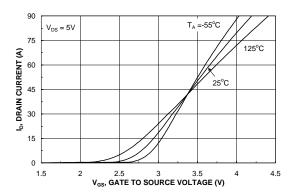


Figure 5. Transfer Characteristics

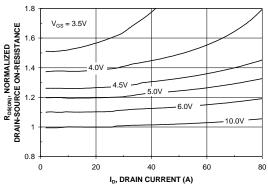


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

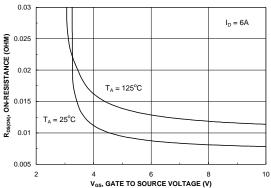


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

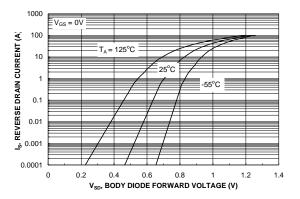
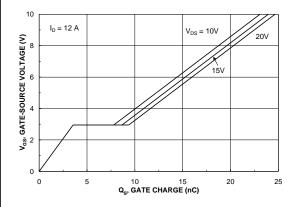


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Characteristics



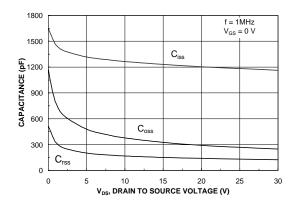
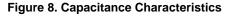
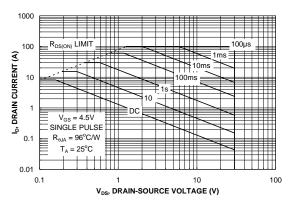


Figure 7. Gate Charge Characteristics





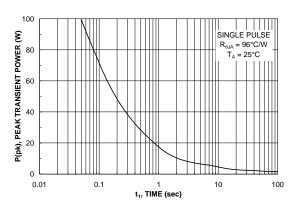


Figure 9. Maximum Safe Operating Area



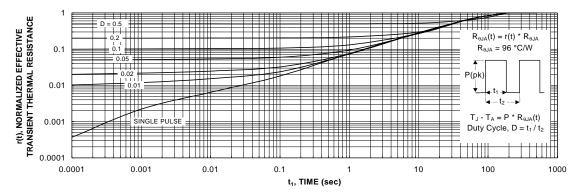


Figure 11. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.







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Definition of Terms					
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